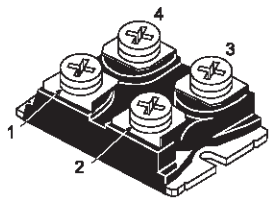
STE26NA90

N - CHANNEL 900V - 0.25Ω - 26A - ISOTOP FAST POWER MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STE26NA90	900 V	< 0.3 Ω	26 A

- TYPICAL $R_{DS(on)}$ = 0.25 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- GATE CHARGE MINIMIZED
- REDUCED VOLTAGE SPREAD

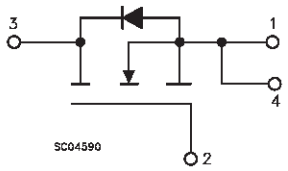


ISOTOP

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY AND MOTOR DRIVE

INTERNAL SCHEMATIC DIAGRAM



Obsolete Product(s) - Obsolete Product(s)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	900	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	900	V
V_{GS}	Gate-source Voltage	± 30	V
I_D	Drain Current (continuous) at T_c = 25 °C	26	A
I_D	Drain Current (continuous) at T_c = 100 °C	16.2	A
I_{DM}(•)	Drain Current (pulsed)	104	A
P_{tot}	Total Dissipation at T_c = 25 °C	450	W
	Derating Factor	3.6	W/°C
T_{stg}	Storage Temperature	-55 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C
V_{ISO}	Insulation Withstand Voltage (AC-RMS)	2500	V

(•) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.27	°C/W
$R_{thc\text{-}h}$	Thermal Resistance Case-heatsink With Conductive Grease Applied	Max	0.05	°C/W

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	13	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	3000	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 500 µA V_{GS} = 0	900			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_c = 125 °C			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 30 V			± 200	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ I_D = 1 mA	2.25	3	3.75	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 13 A		0.25	0.3	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	26			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 13 A	15			S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		13600 1130 270	17700 1470 350	pF pF pF

Obsolete Product(s) - Obsolete Product(s)

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 450 V I_D = 12 A R_G = 4.7 Ω V_{GS} = 10 V (see test circuit, figure 3)		40 52	56 73	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 720 V I_D = 26 A V_{GS} = 10 V		470 43 226	660	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 720 V I_D = 26 A R_G = 4.7 Ω V_{GS} = 10 V (see test circuit, figure 5)		108 25 145	152 35 203	ns ns ns

SOURCE DRAIN DIODE

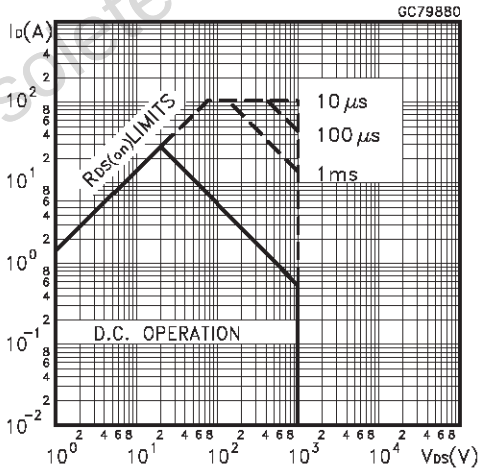
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				26 104	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 26 A V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 26 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C (see test circuit, figure 5)		1.3 38 58		µs µC A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

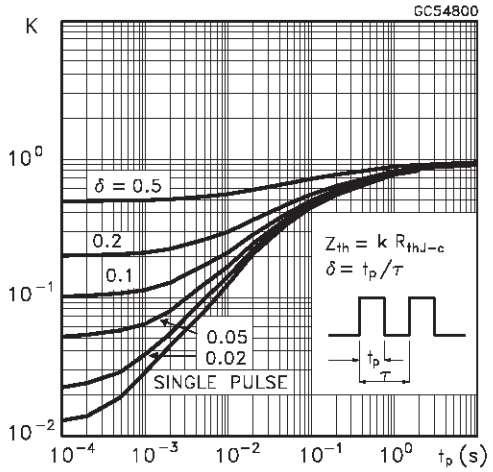
(•) Pulse width limited by safe operating area

Obsolete Product(s) - Obsolete Product(s)

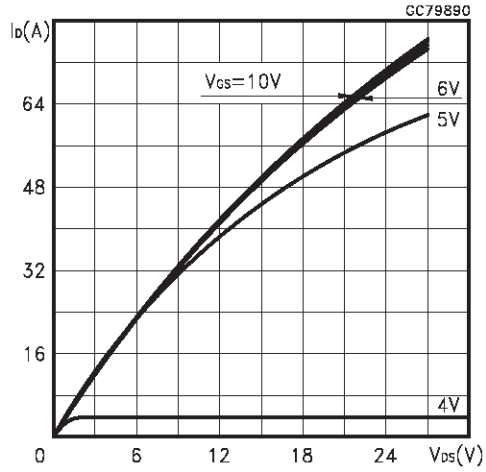
Safe Operating Area



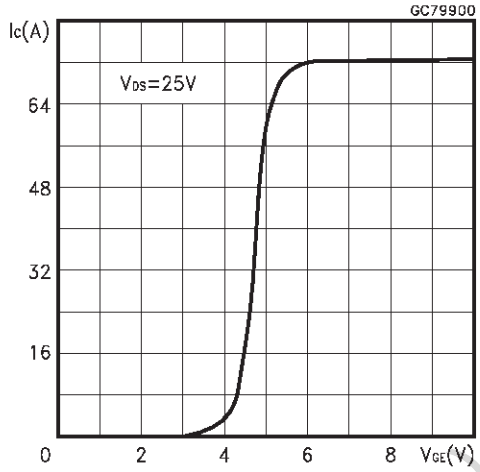
Thermal Impedance



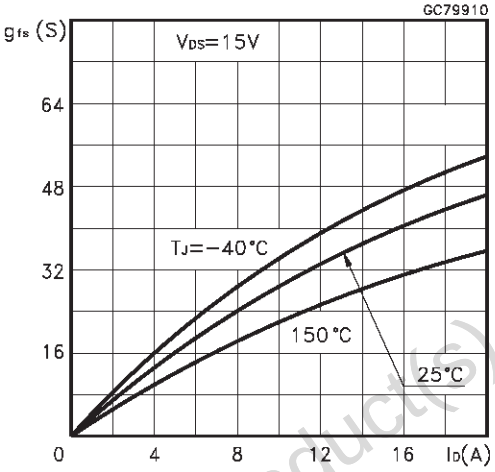
Output Characteristics



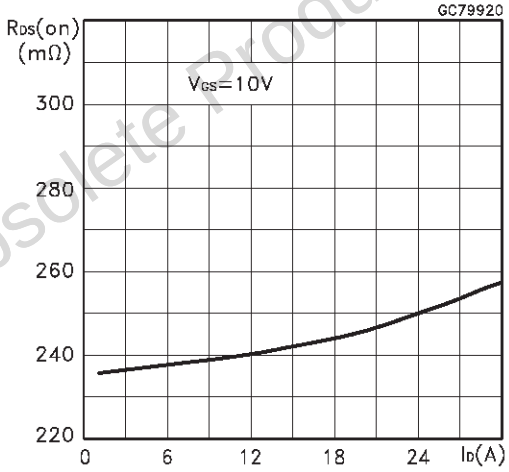
Transfer Characteristics



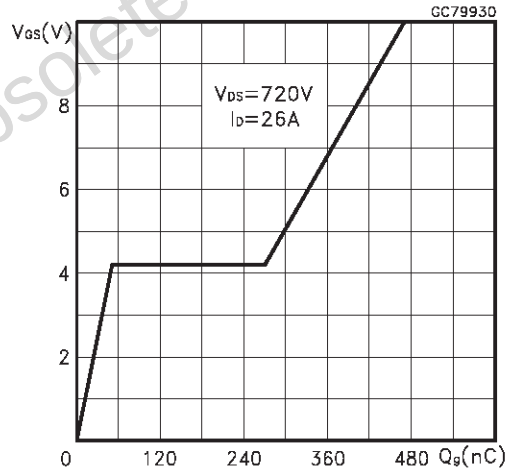
Transconductance



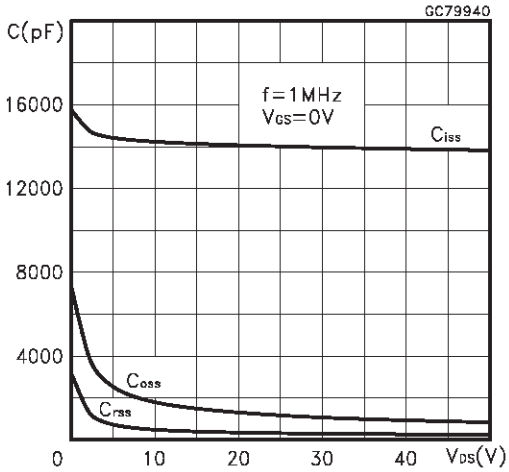
Static Drain-source On Resistance



Gate Charge vs Gate-source Voltage

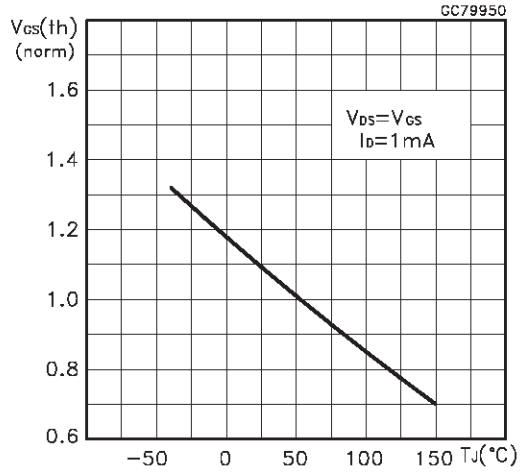


Capacitance Variations

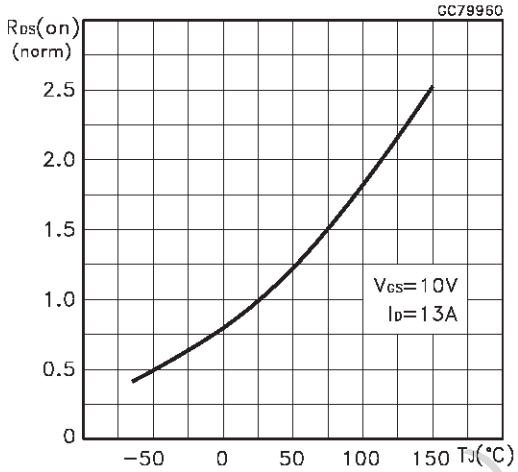


Obsolete Product(s) - Obsolete Product(s)

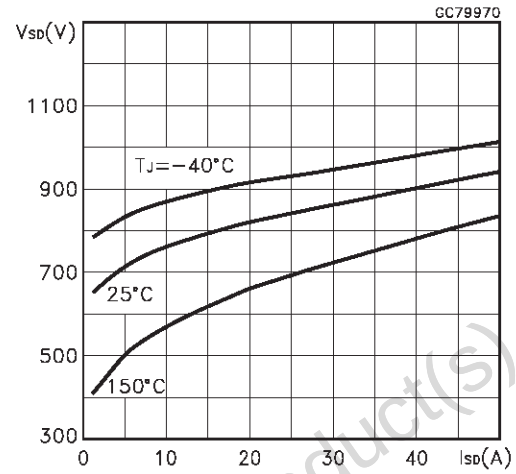
Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Obsolete Product(s) - Obsolete Product(s)

Fig. 1: Unclamped Inductive Load Test Circuit

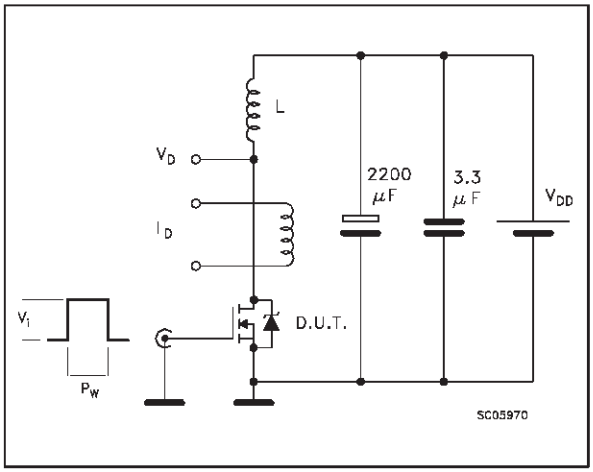


Fig. 2: Unclamped Inductive Waveform

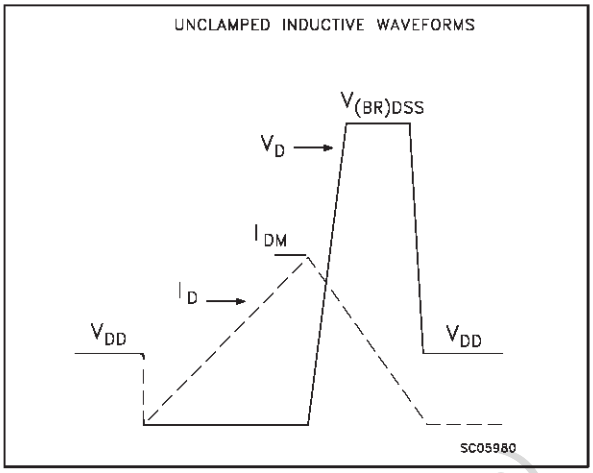


Fig. 3: Switching Times Test Circuits For Resistive Load

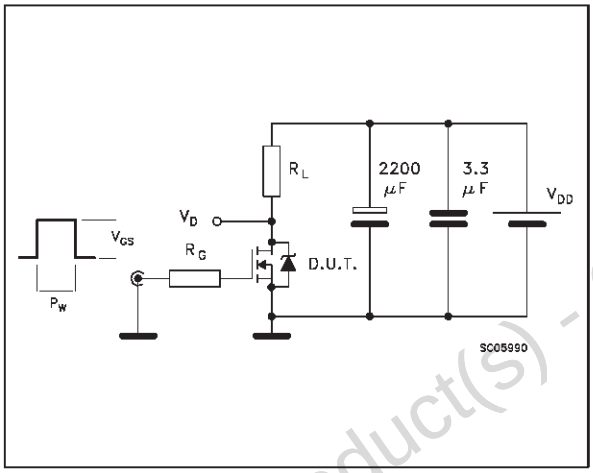


Fig. 4: Gate Charge test Circuit

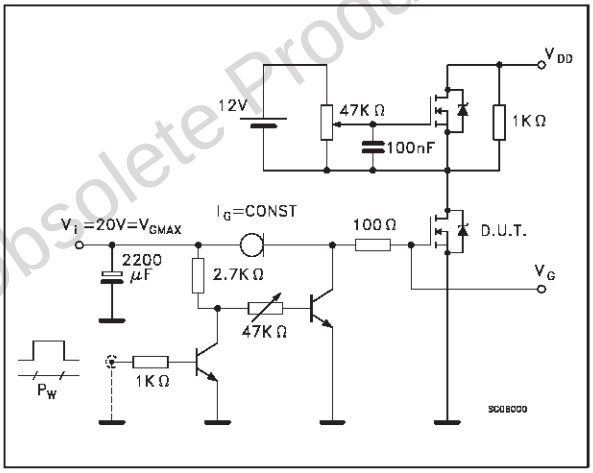
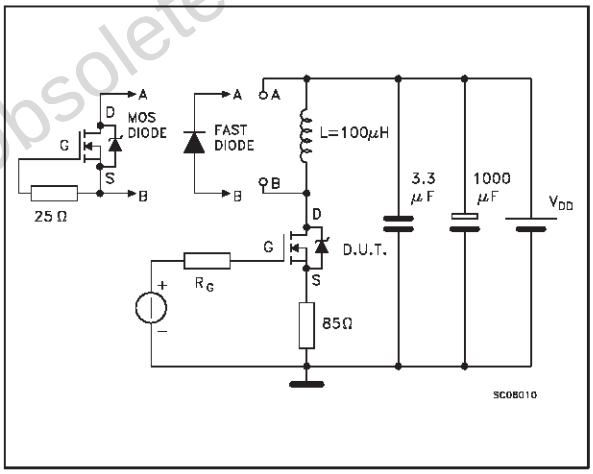


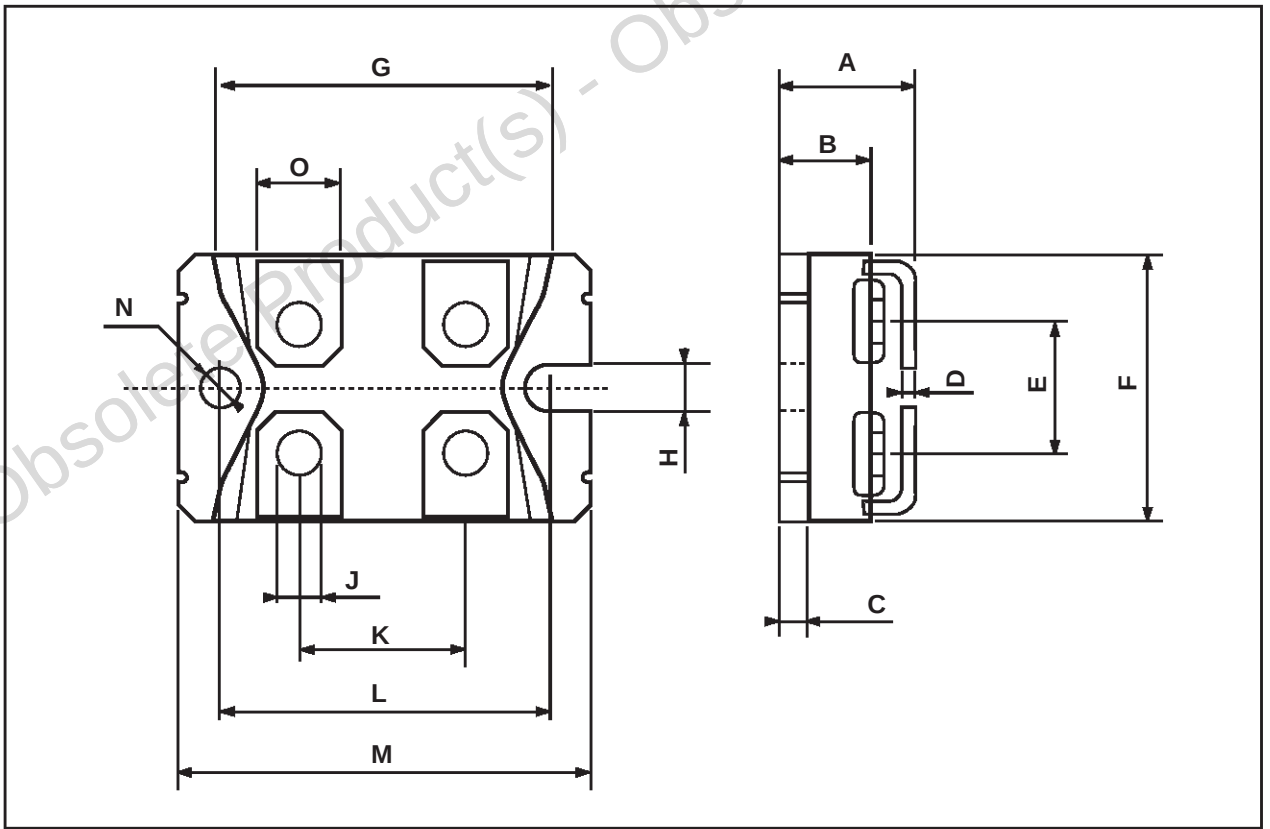
Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



Obsolete Product(s) - Obsolete Product(s)

ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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